

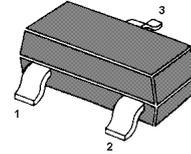
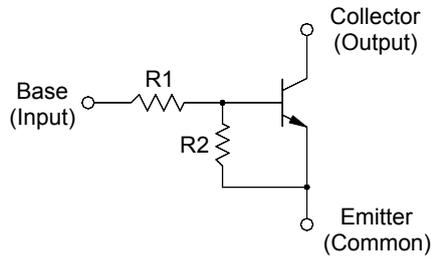
MMBTRC101SS...MMBTRC106SS

NPN Silicon Epitaxial Planar Transistor

for switching and interface circuit and drive circuit applications

Features

- With built-in bias resistors
- Simplify circuit design
- Reduce a quantity of parts and manufacturing process



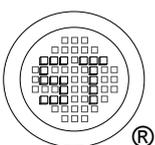
1. Base 2. Emitter 3. Collector
TO-236 Plastic Package

Resistor Values

Type	R1 (KΩ)	R2 (KΩ)
MMBTRC101SS	4.7	4.7
MMBTRC102SS	10	10
MMBTRC103SS	22	22
MMBTRC104SS	47	47
MMBTRC105SS	2.2	47
MMBTRC106SS	4.7	47

Absolute Maximum Ratings ($T_a = 25^\circ\text{C}$)

Parameter		Symbol	Value	Unit
Output Voltage		V_o	50	V
Input Voltage	MMBTRC101SS	V_i	20, -10	V
	MMBTRC102SS		30, -10	
	MMBTRC103SS		40, -10	
	MMBTRC104SS		40, -10	
	MMBTRC105SS		12, -5	
	MMBTRC106SS		20, -5	
Output Current		I_o	100	mA
Total Power Dissipation		P_{tot}	200	mW
Junction Temperature		T_j	150	$^\circ\text{C}$
Storage Temperature Range		T_{stg}	- 55 to + 150	$^\circ\text{C}$



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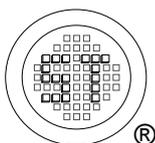
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Characteristics at $T_a = 25\text{ }^\circ\text{C}$

Parameter	Symbol	Min.	Typ.	Max.	Unit
DC Current Gain at $V_O = 5\text{ V}$, $I_O = 10\text{ mA}$	G _I	30	-	-	-
MMBTRC101SS		50	-	-	-
MMBTRC102SS		70	-	-	-
MMBTRC103SS		80	-	-	-
MMBTRC104SS		80	-	-	-
MMBTRC105SS MMBTRC106SS		80	-	-	-
Output Cutoff Current at $V_O = 50\text{ V}$	I _{O(OFF)}	-	-	500	nA
Input Current at $V_I = 5\text{ V}$	I _I	-	-	1.8	mA
MMBTRC101SS		-	-	0.88	
MMBTRC102SS		-	-	0.36	
MMBTRC103SS		-	-	0.18	
MMBTRC104SS		-	-	3.6	
MMBTRC105SS MMBTRC106SS		-	-	1.8	
Output Voltage at $I_O = 10\text{ mA}$, $I_I = 0.5\text{ mA}$	V _{O(ON)}	-	-	0.3	V
Input Voltage (ON) at $V_O = 0.2\text{ V}$, $I_O = 5\text{ mA}$	V _{I(ON)}	-	-	2	V
MMBTRC101SS		-	-	2.4	
MMBTRC102SS		-	-	3	
MMBTRC103SS		-	-	5	
MMBTRC104SS		-	-	1.1	
MMBTRC105SS MMBTRC106SS		-	-	1.3	
Input Voltage (OFF) at $V_O = 5\text{ V}$, $I_O = 0.1\text{ mA}$	V _{I(OFF)}	1	-	-	V
MMBTRC101SS~104SS MMBTRC105SS~106SS		0.5	-	-	
Transition Frequency at $V_O = 10\text{ V}$, $I_O = 5\text{ mA}$	f _T ¹⁾	-	200	-	MHz

¹⁾ Characteristic of transistor only.

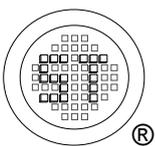
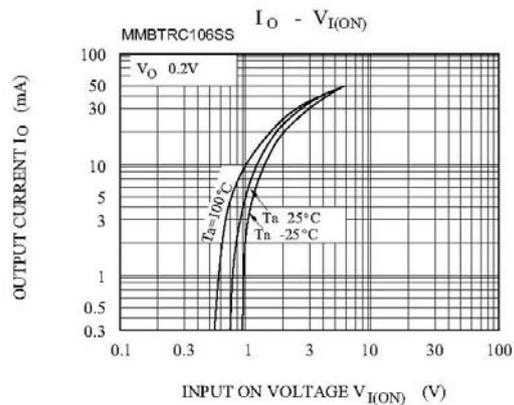
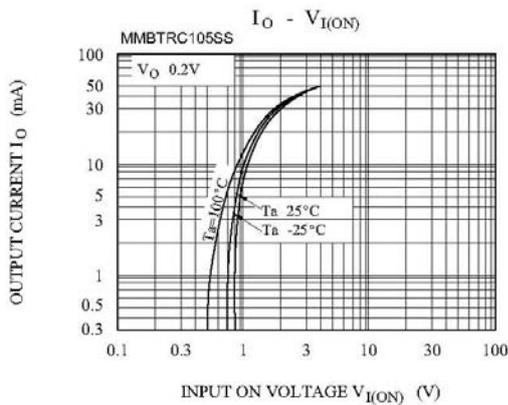
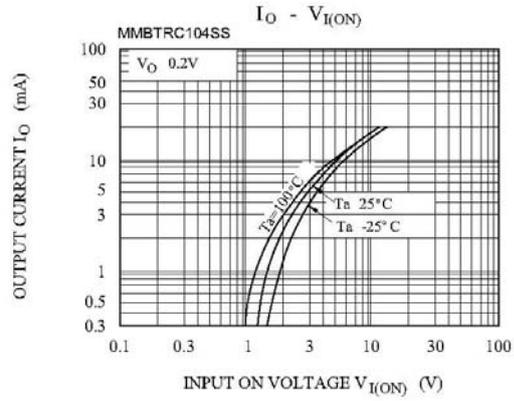
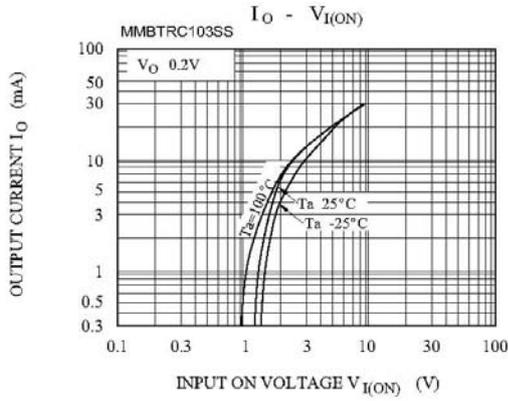
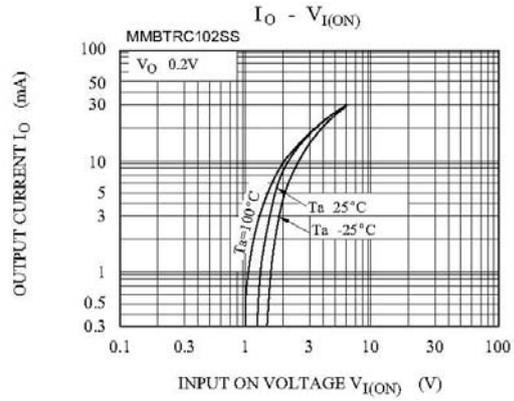
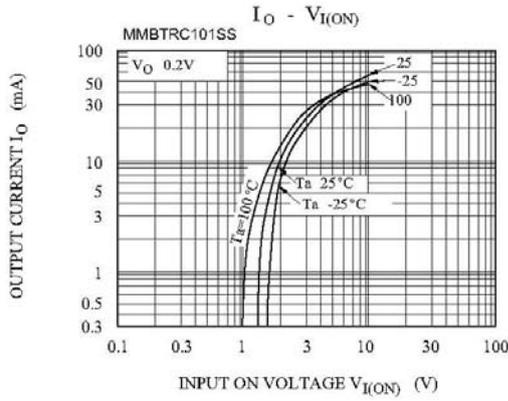


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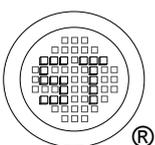
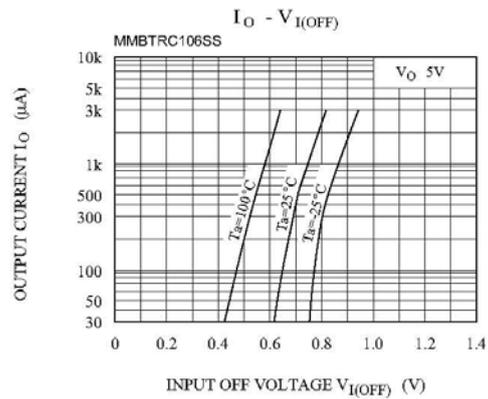
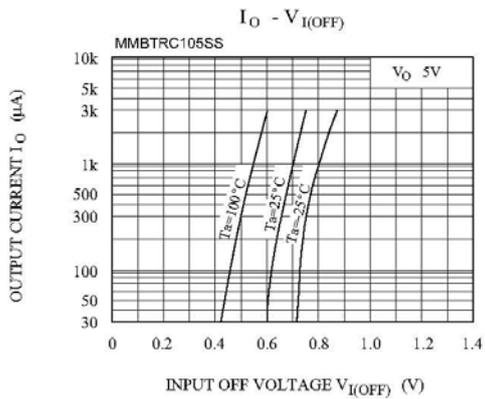
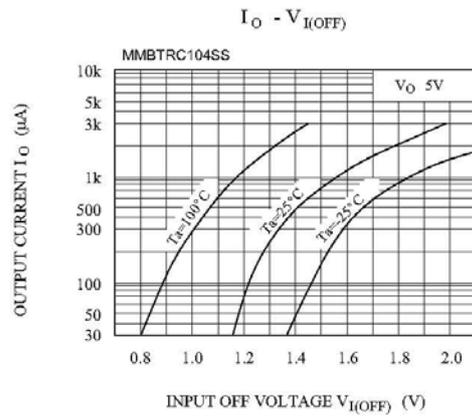
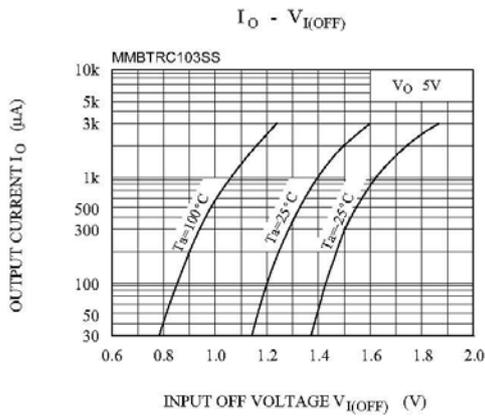
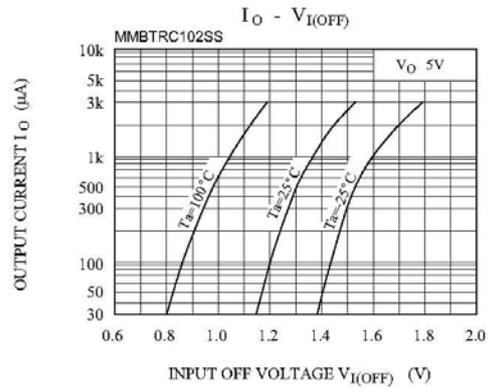
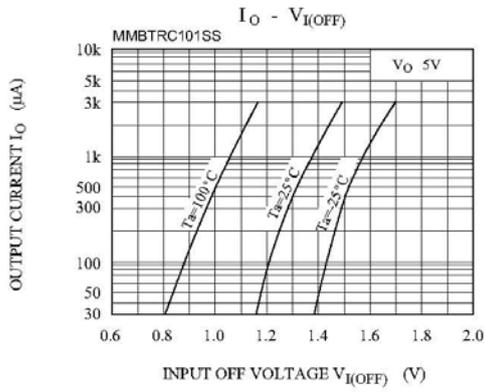
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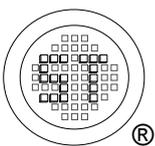
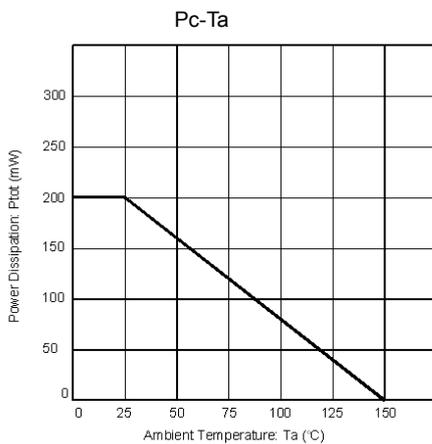
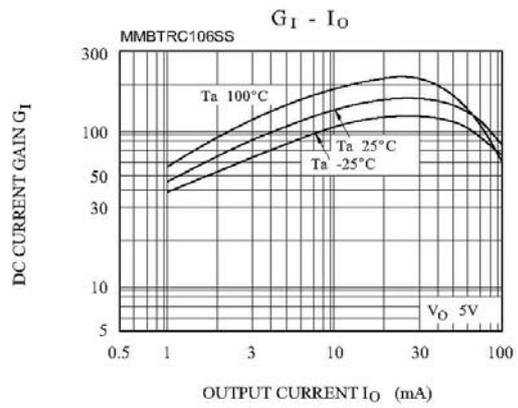
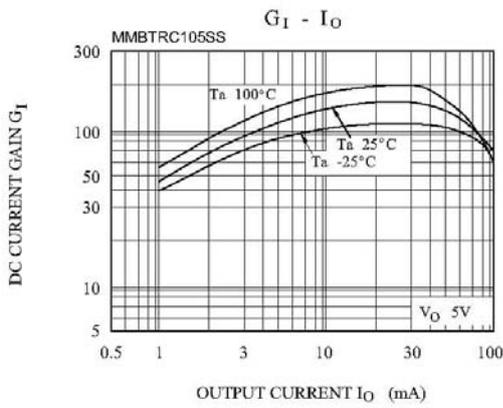
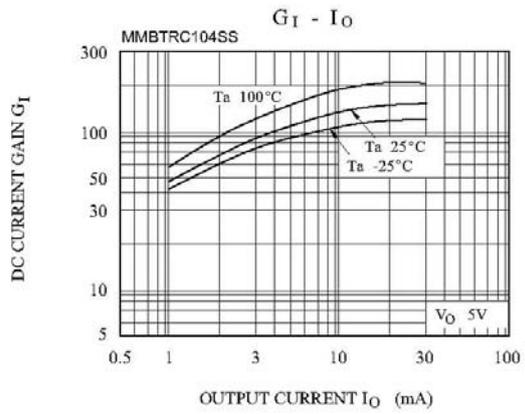
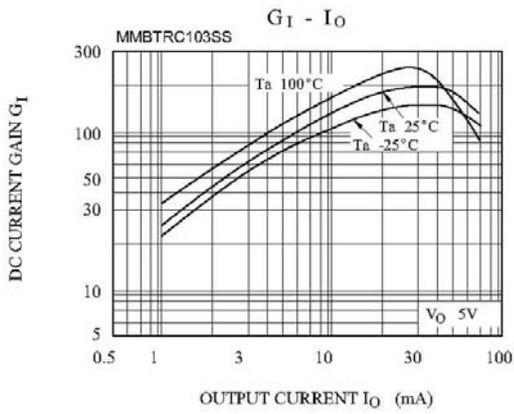
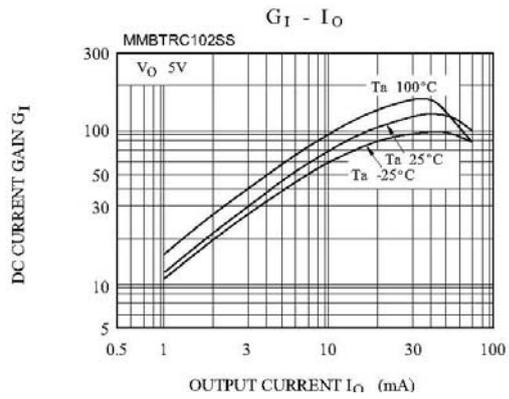
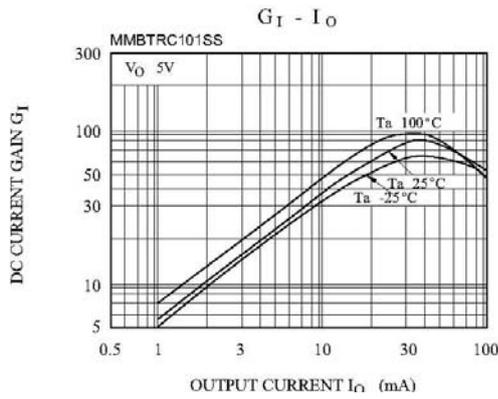
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